HTJ440P03 P-1

30V P-Ch Power MOSFET

V_{DS}		-30	V
$R_{DS(on),typ}$	V_{GS}=10V	32	mΩ
$R_{DS(on),typ}$	V_{GS}=4.5V	39	mΩ
$R_{DS(on),typ}$	V_{GS}=2.5V	60	mΩ
$I_{D\ (Sillicon\ Limited)}$		-4	A

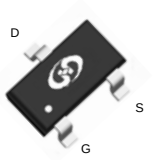
Feature

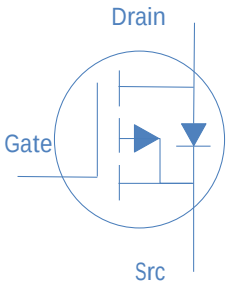
- High Speed Power Switching, Logic Level
- Enhanced Avalanche Ruggedness
- Lead Free, Halogen Free

Application

- Load Switches
- Hard Switching and High Speed Circuit
- BLDC Motor

SOT-23





Part Number	Package	Marking
HTJ440P03	SOT-23	26

Absolute Maximum Ratings at T_j=25 (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	I_D	T_A=25	-4	A
		T_A=70	-3	
Drain to Source Voltage	V_{DS}	-	-30	V
Gate to Source Voltage	V_{GS}	-	±12	V
Pulsed Drain Current	I_{DM}	-	-16	A
Power Dissipation	P_D	T_A=25	1.25	W
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to150	

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	100	/W

Fig 1. Typical Output Characteristics	Figure 2. On-Resistance vs. Gate-Source Voltage

Figure 3. Gate Threshold Voltage v.s. Junction Temperature	Figure 4. Normalized On-Resistance vs. Junction Temperature

Figure 5. Typical Source-Drain Diode Forward Voltage

Figure 6. Typical Gate-Charge vs. Gate-to-Source Voltage

Figure 7. Typical Capacitance vs. Drain-to-Source Voltage

Figure 8. Maximum Safe Operating Area

Figure 9. Maximun Drain Current vs. Case Temperature

Figure 10. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient

Inductive switching Test	

Gate Charge Test	

Uclamped Inductive Switching (UIS) Test	

Diode Recovery Test	

Package Outline

SOT-23, 3leads